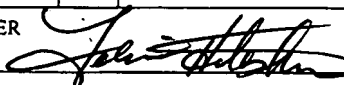


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IAP9 Rec'd PCT/PTO 13 DEC 2005

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126274		APPLICATION NO. New National Stage Patent Application of PCT/JP2004/007350	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANTS Masahiro SAKURADA et al.			
				FILING DATE December 13, 2005			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
A	FH.	1	JP A 2003-002786 w/abst. & trans	01/08/2003	JAPAN	-	-
A	FH.	2	JP A 08-268794 w/abst. & trans	10/15/1996	JAPAN	-	-
	FH.	3	JP A 08-330316 w/abst. & trans	12/13/1996	JAPAN	-	-
	FH.	4	JP A 2000-063196 w/abst. & trans	02/29/2000	JAPAN	-	-
	FH.	5	JP A 2000-313691 w/abst. & trans	11/14/2000	JAPAN	-	-
	FH.	6	JP A 2002-338389 w/abst. & trans	11/27/2002	JAPAN	-	-
	FH.	7	JP A 11-147786 w/abst. & trans	06/02/1999	JAPAN	-	-
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	FH.	8	V. V. Voronkov, " The mechanism of Swirl Defects formation in Silicon," Journal of Crystal Growth, 59 (1982), 625-643.				
	FH.	9	F. Dupret et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No 9, pp. 1849-1871, 1990.				
EXAMINER				DATE CONSIDERED			
				6/22/2007			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 13, 2005